

### Features

70Watts peak pulse power ( $t_p = 8/20\mu s$ )  
 Tiny DFN1006 package  
 Bidirectional configurations  
 Solid-state silicon-avalanche technology  
 Low clamping voltage  
 Low leakage current  
 Low capacitance ( $C_J = 0.25\text{pF}$  typ. IO to I<sub>O</sub>)  
 Protection one data/power line to:  
 IEC 61000-4-2  $\pm 20\text{kV}$  contact  $\pm 20\text{kV}$  air  
 IEC 61000-4-4 (EFT) 40A (5/50ns)  
 IEC 61000-4-5 (Lightning) 4A (8/20 $\mu s$ )

### Applications

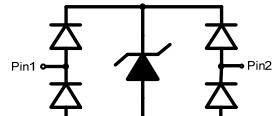
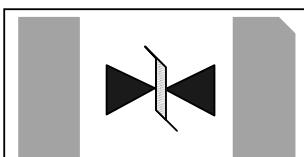
Cell Phone Handsets and Accessories  
 Microprocessor based equipment  
 Personal Digital Assistants (PDA's)  
 Notebooks, Desktops, and Servers  
 Portable Instrumentation



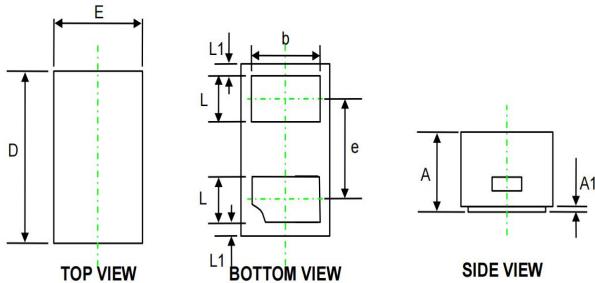
### Mechanical Data

DFN1006 package  
 Molding compound flammability rating: UL 94V-0  
 Packaging: Tape and Reel  
 RoHS/WEEE Compliant

### Schematic & PIN Configuration



### DFN1006



Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	0.44	0.47	0.50
A1	0.00	0.03	0.05
D	0.95	1.00	1.08
E	0.55	0.60	0.68
b	0.40	0.50	0.60
e	-	0.65	-
L	0.20	0.25	0.30
L1	0.05 REF.		

Dimensions in inches and (millimeters)

### Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	P <sub>PP</sub>	70	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ ) (note1)	I <sub>PP</sub>	4.0	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	20 20	kV
Lead Soldering Temperature	T <sub>L</sub>	260(10seconds)	°C
Junction Temperature	T <sub>J</sub>	-55 to + 125	°C
Storage Temperature	T <sub>stg</sub>	-55 to + 125	°C

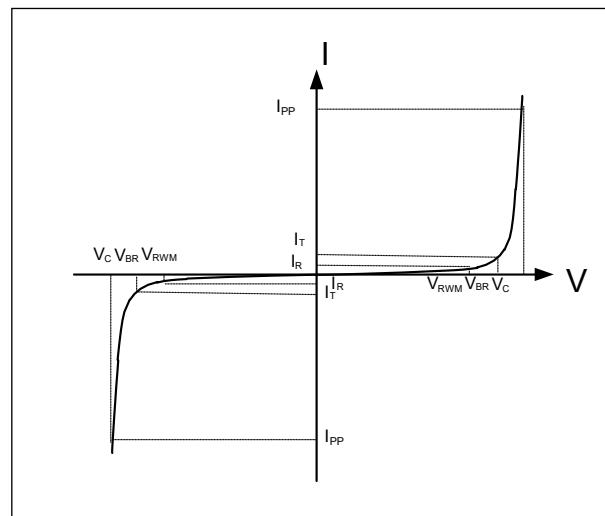
# ESD5311X

## Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T = 1\text{mA}$	6.2			V
Reverse Leakage Current	$I_R$	$V_{RWM} = 5\text{V}, T = 25^\circ\text{C}$			100	nA
Peak Pulse Current	$I_{PP}$	$t_p = 8/20\mu\text{s}$			4.0	A
Clamping Voltage	$V_C$	$I_{PP} = 4\text{A}, t_p = 8/20\mu\text{s}$			23	V
Junction Capacitance	$C_j$	$\text{IO to IO}$ $V_R = 0\text{V}, f = 1\text{MHz}$		0.25	0.45	pF

## Electrical Parameters (TA = 25°C unless otherwise noted)

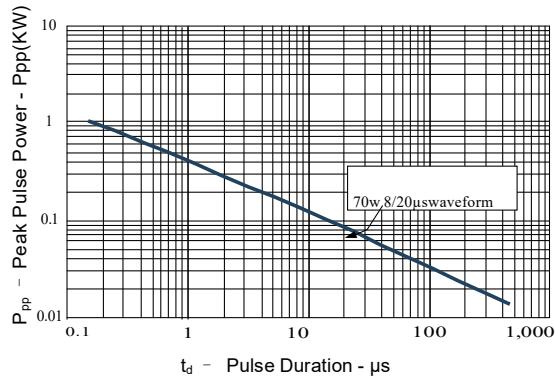
Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current



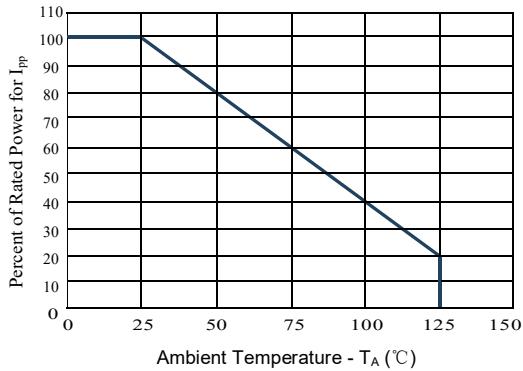
Note: 8/20μs pulse waveform.

## RATING AND CHARACTERISTIC CURVES (ESD5311X)

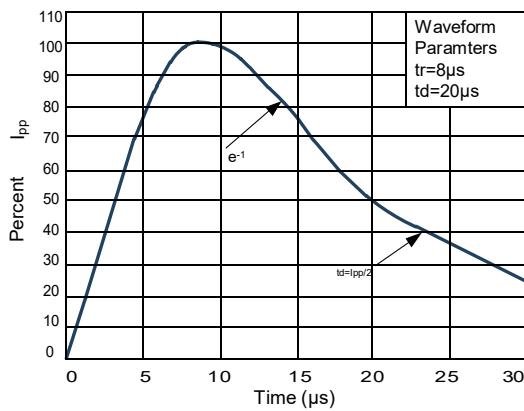
**Figure 1: Peak Pulse Power vs. Pulse Time**



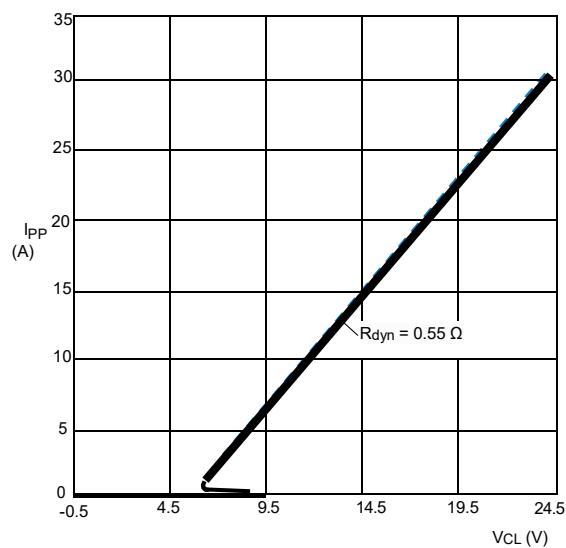
**Figure 2: Power Derating Curve**



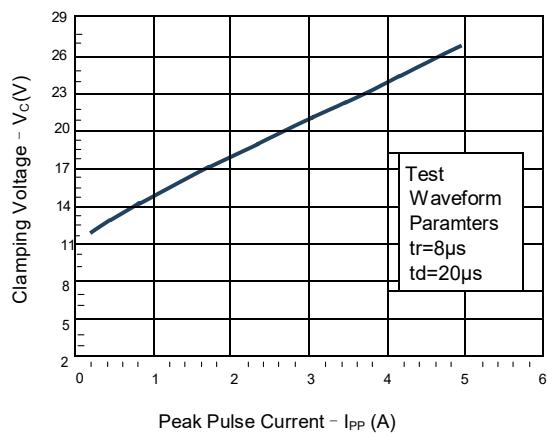
**Figure3: Pulse Waveform**



**Figure5: Positive Clamping voltage (TLP)**



**Figure 4: Clamping Voltage vs.Ipp**



**Figure5: Negative Clamping voltage (TLP)**

